

60V P-Channel Enhancement Mode MOSFET - ESD Protected

Voltage

-60 V

Current

-250mA

Features

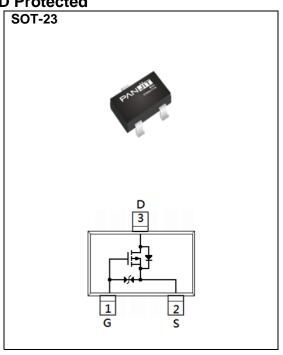
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-500mA<4\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_{D}@-200mA<6\Omega$
- Advanced Trench Process Technology
- ESD Protected
- AEC-Q101 qualified
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0084 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V _G s	<u>+</u> 20		
Continuous Drain Current(Note 4)	T _A =25°C	I _D	-250	mA	
Pulsed Drain Current(Note 1)	T _A =25°C	I _{DM}	-1000		
Power Dissipation	T _A =25°C		500	mW	
	Derate above 25°C	P _D	4	mW/°C	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Thermal Resistance - Junction to Ambient ^(Note 4)		ReJA	250	°C/W	



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA V _{DS} =V _{GS} , I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	V _{GS(th)}		-0.8	-1.4	-2	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-500mA	-	2.1	4	Ω
		V _{GS} =-4.5V,I _D =-200mA	-	2.5	6	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}		-	-	<u>+</u> 10	
Dynamic ^(Note 6)						
Total Gate Charge	Q_g	V _{DS} =-30V, I _D =-250mA, V _{GS} =-10V	-	1.86	3	nC
Gate-Source Charge	Q_{gs}		-	0.34	-	
Gate-Drain Charge	Q_{gd}		-	0.27	-	
Input Capacitance	Ciss	V _{DS} =-30V, V _{GS} =0V, f=1MHz	-	34.4	60	pF
Output Capacitance	Coss		-	7.3	15	
Reverse Transfer Capacitance	Crss		-	2.4	5	
Turn-On Delay Time	td _(on)	V_{DD} =-30V, I_{D} =-250mA, V_{GS} =-10V, R_{G} =6 $\Omega^{(Note 1,2)}$	-	4.6	-	
Turn-On Rise Time	tr		-	3.1	-	ns
Turn-Off Delay Time	td _(off)		-	40	-	
Turn-Off Fall Time	tf	KG=012(1888 1,2)	-	23	-	
Drain-Source Diode						
Continuous Diode Forward Current	ls	T _A =25 °C	-	-	-250	mA
Continuous Diode Forward Current	Isм	1A=20 C	-	-	-1000	mA
Diode Forward Voltage	V _{SD}	I _S =-500mA,V _{GS} =0V	-	-0.95	-1.3	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}C$. Ratings are based on low frequency and duty cycles to keep initial $T_{J}=25^{\circ}C$.
- 4. The maximum current rating is package limited.
- 5. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

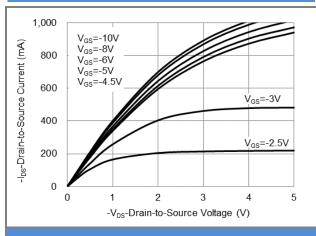


Fig.1 On-Region Characteristics

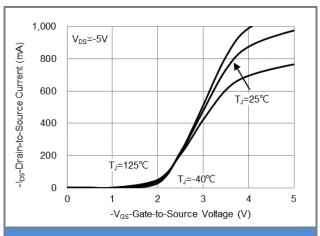


Fig.2 Transfer Characteristics

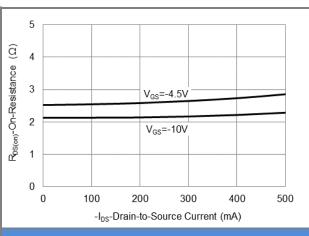


Fig.3 On-Resistance vs. Drain Current

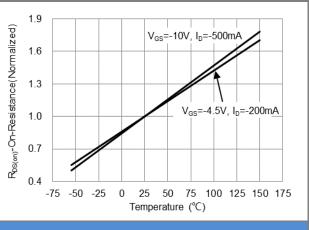
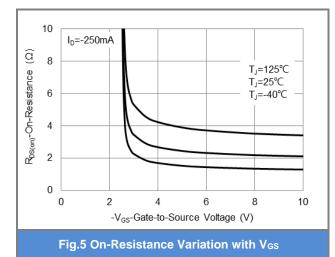


Fig.4 On-Resistance vs. Junction temperature



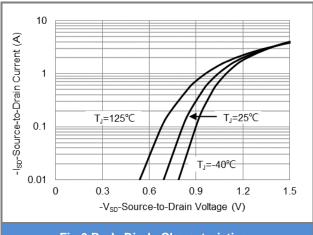


Fig.6 Body Diode Characteristics



TYPICAL CHARACTERISTIC CURVES

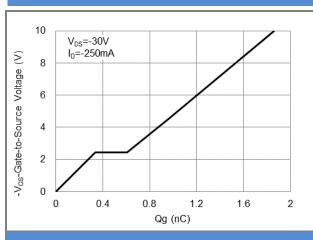


Fig.7 Gate-Charge Characteristics

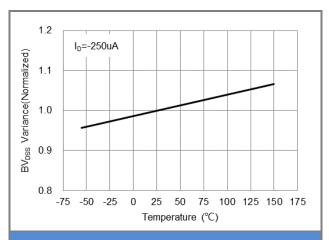


Fig.8 Breakdown Voltage Variation vs. Temperature

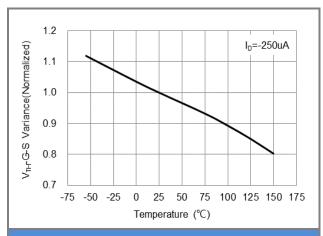


Fig.9 Threshold Voltage Variation with Temperature

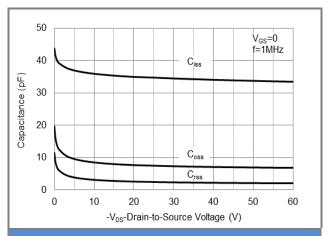


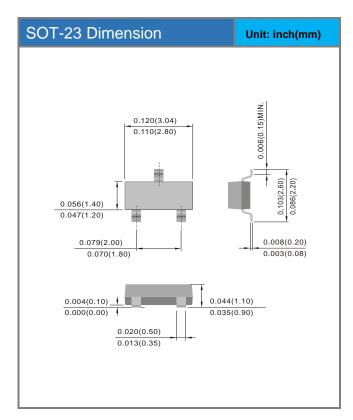
Fig.10 Capacitance vs. Drain-Source Voltage

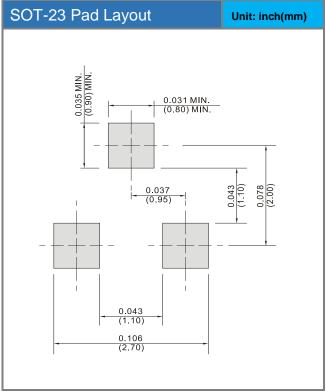


Product and Packing Information

Part No.	Package Type	Packing Type	Marking
BSS84E-AU	SOT-23	3K pcs / 7" reel	84E

Packaging Information & Mounting Pad Layout







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